

AMENDMENT TO THE SPECIFICATION

The paragraph beginning on page 2, line 25 and ending on page 3, line 5 has been amended as follows:

--The present inventor tentatively defined a resist pattern by exposing a resist film to EUV radiation and then patterned a film on a substrate by dry-etching it using the resist pattern obtained. As a result, [[I]] the present inventor found that the walls of the patterned film showed a non-negligibly high degree of roughness.--

The paragraph beginning on page 3, line 13 has been amended as follows:

--[[I]] The present inventor carried out intensive research to understand why the walls of a patterned film showed an increased degree of roughness where the patterned film had been formed by dry-etching an original film using, as a mask, a resist pattern defined through exposure of a resist film to EUV radiation. As a result, [[I]] the present inventor found the following.--

The paragraph beginning on page 4, line 20 has been amended as follows:

--[[I]] The present inventor acquired the basic idea of this invention from these findings.--